

Abstract of the Disclosure

SUBSTRATE PROCESSING APPARATUS AND SUBSTRATE PROCESSING
METHOD

5 A spin chuck on which a wafer is mounted is
divided into a plurality of regions concentrically in a
radial direction, and different temperatures are set
for each of the regions so that the temperature
gradually increases from the outer periphery to the
center. The wafer is placed on this spin chuck, and a
processing solution is applied to the wafer and spread
over the wafer by centrifugal force, whereby the
10 vaporization of a solvent of the processing solution
which is spread on the outer periphery of the wafer is
suppressed, and hence the timing of drying of the
processing solution within the surface of the wafer can
be made uniform. Consequently, a coating film with a
15 uniform thickness within the wafer surface can be
obtained.

Fig. 1